

America Semiconductor



"In America Semi We Trust"

MANUFACTURER OF WORLD CLASS HIGH POWER SEMICONDUCTORS

America Semiconductor

Silicon Power Schottky Diode

- Features**
- High Surge Capability
 - Types up to 100 V V_{RRM}

MBR60020CT thru MBR60040CTR

$V_{RRM} = 20\text{ V} - 100\text{ V}$
 $I_F = 600\text{ A}$

Twin Tower Package



Maximum ratings, at $T_J = 25^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR60020CT (R)	MBR60030CT (R)	MBR60035CT (R)	MBR60040CT (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		20	30	35	40	V
RMS reverse voltage	V_{RMS}		14	21	25	28	V
DC blocking voltage	V_{DC}		20	30	35	40	V
Continuous forward current	I_F	$T_C \leq 100^\circ\text{C}$	600	600	600	600	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25^\circ\text{C}, t_p = 8.3\text{ ms}$	4000	4000	4000	4000	A
Operating temperature	T_J		-40 to 150	-40 to 150	-40 to 150	-40 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to 175	-40 to 175	-40 to 175	-40 to 175	$^\circ\text{C}$

Electrical characteristics, at $T_J = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR60020CT (R)	MBR60030CT (R)	MBR60035CT (R)	MBR60040CT (R)	Unit
Diode forward voltage	V_F	$I_F = 300\text{ A}, T_J = 25^\circ\text{C}$	0.75	0.75	0.75	0.75	V
Reverse current	I_R	$V_R = 20\text{ V}, T_J = 25^\circ\text{C}$	1	1	1	1	mA
		$V_R = 20\text{ V}, T_J = 125^\circ\text{C}$	20	20	20	20	mA

Thermal characteristics

Parameter	Symbol	Conditions	MBR60020CT (R)	MBR60030CT (R)	MBR60035CT (R)	MBR60040CT (R)	Unit
Thermal resistance, junction - case	$R_{\theta JC}$		0.12	0.12	0.12	0.12	$^\circ\text{C/W}$

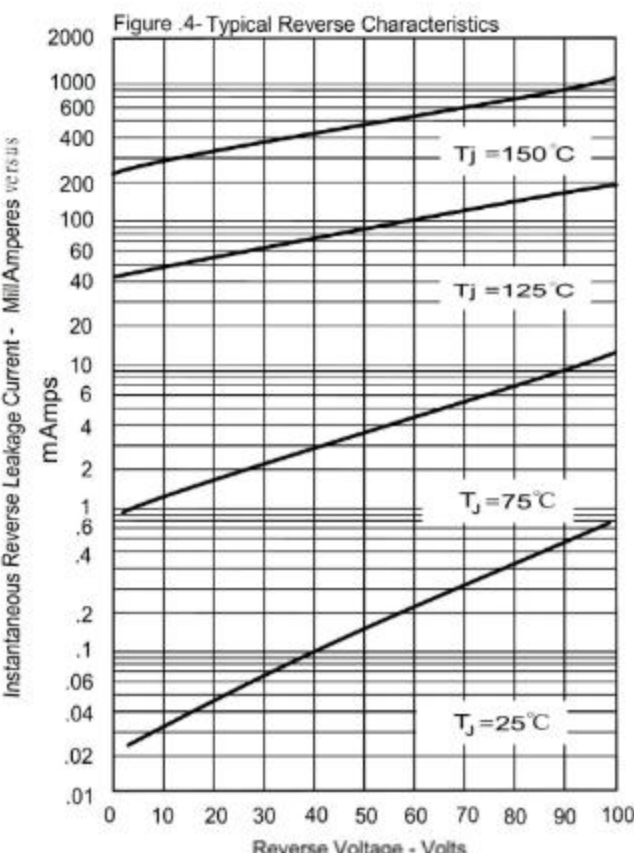
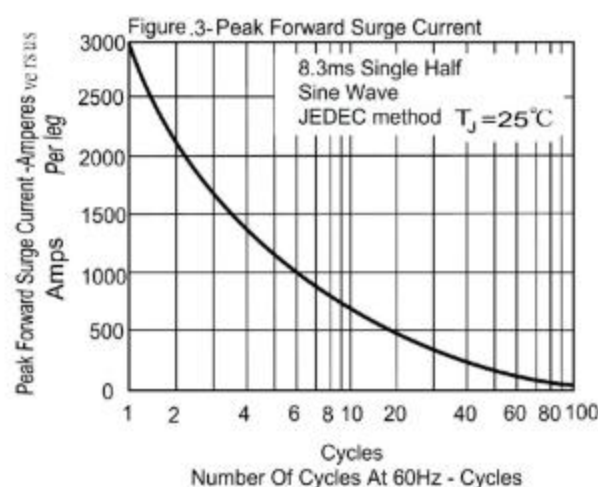
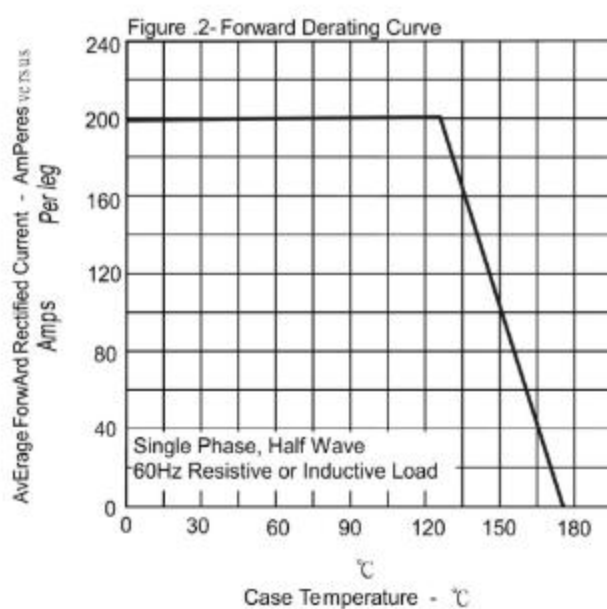
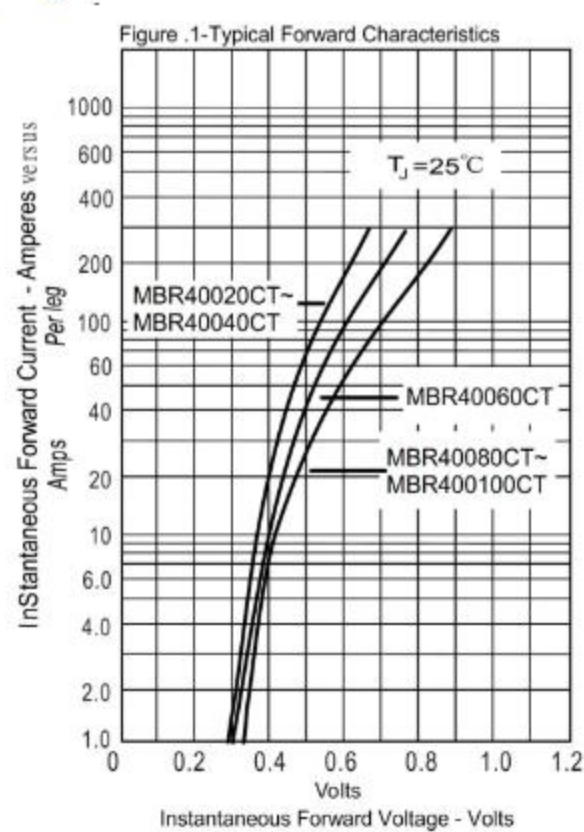


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MBR60020CT thru MBR60040CTR



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